



ON Semiconductor®

BD135 / 137 / 139

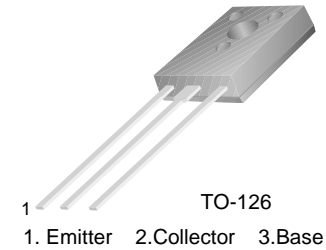
NPN Epitaxial Silicon Transistor

Features

- Complement to BD136, BD138 and BD140 respectively

Applications

- Medium Power Linear and Switching



Ordering Information

| Part Number | Marking | Package | Packing Method |
|-------------|----------|-----------|----------------|
| BD13516S | BD135-16 | TO-126 3L | Bulk |
| BD1356STU | BD135-6 | | Rail |
| BD13510STU | BD135-10 | | Rail |
| BD13516STU | BD135-16 | | Bulk |
| BD13716STU | BD137-16 | | Rail |
| BD13710STU | BD137-10 | | Bulk |
| BD13716S | BD137-16 | | Rail |
| BD13916STU | BD139-16 | | Bulk |
| BD13910S | BD139-10 | | Rail |
| BD13916S | BD139-16 | | Bulk |
| BD1396STU | BD139-6 | | Rail |
| BD13910STU | BD139-10 | | Rail |

BD135 / 137 / 139 — NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_C = 25^\circ\text{C}$ unless otherwise noted.

| Symbol | Parameter | Value | Units |
|-----------|---------------------------|--------------------------|------------------|
| V_{CBO} | Collector-Base Voltage | BD135 | 45 |
| | | BD137 | 60 |
| | | BD139 | 80 |
| V_{CEO} | Collector-Emitter Voltage | BD135 | 45 |
| | | BD137 | 60 |
| | | BD139 | 80 |
| V_{EBO} | Emitter-Base Voltage | 5 | V |
| I_C | Collector Current (DC) | 1.5 | A |
| I_{CP} | Collector Current (Pulse) | 3.0 | A |
| I_B | Base Current | 0.5 | A |
| P_C | Device Dissipation | $T_C = 25^\circ\text{C}$ | 12.5 |
| | | $T_A = 25^\circ\text{C}$ | 1.25 |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature | - 55 to +150 | $^\circ\text{C}$ |

Electrical Characteristics

Values are at $T_C = 25^\circ\text{C}$ unless otherwise noted.

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Units |
|----------------|--------------------------------------|--|-------|------|------|---------------|
| $V_{CEO(sus)}$ | Collector-Emitter Sustaining Voltage | $I_C = 30\text{ mA}, I_B = 0$ | BD135 | 45 | | |
| | | | BD137 | 60 | | |
| | | | BD139 | 80 | | |
| I_{CBO} | Collector Cut-off Current | $V_{CB} = 30\text{ V}, I_E = 0$ | | | 0.1 | μA |
| I_{EBO} | Emitter Cut-off Current | $V_{EB} = 5\text{ V}, I_C = 0$ | | | 10 | μA |
| h_{FE1} | DC Current Gain | $V_{CE} = 2\text{ V}, I_C = 5\text{ mA}$ | 25 | | | |
| h_{FE2} | | $V_{CE} = 2\text{ V}, I_C = 0.5\text{ A}$ | 25 | | | |
| h_{FE3} | | $V_{CE} = 2\text{ V}, I_C = 150\text{ mA}$ | 40 | | 250 | |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C = 500\text{ mA}, I_B = 50\text{ mA}$ | | | 0.5 | V |
| $V_{BE(on)}$ | Base-Emitter On Voltage | $V_{CE} = 2\text{ V}, I_C = 0.5\text{ A}$ | | | 1 | V |

h_{FE} Classification

| Classification | 6 | 10 | 16 |
|----------------|----------|----------|-----------|
| h_{FE3} | 40 ~ 100 | 63 ~ 160 | 100 ~ 250 |

Typical Performance Characteristics

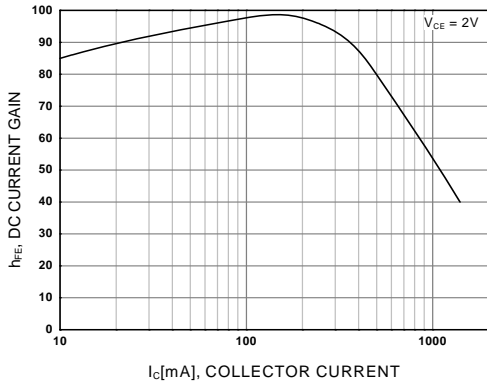


Figure 1. DC current Gain

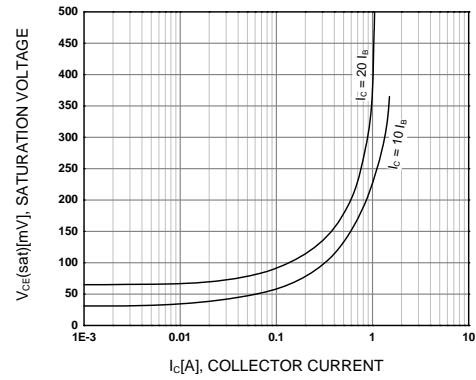


Figure 2. Collector-Emitter Saturation Voltage

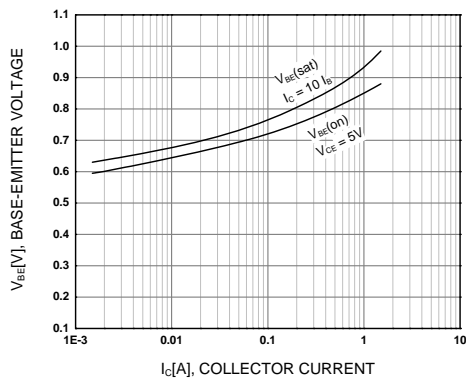


Figure 3. Base-Emitter Voltage

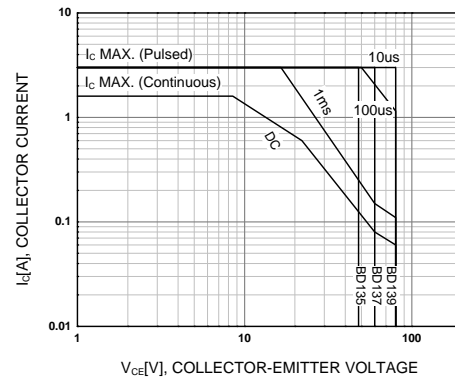


Figure 4. Safe Operating Area

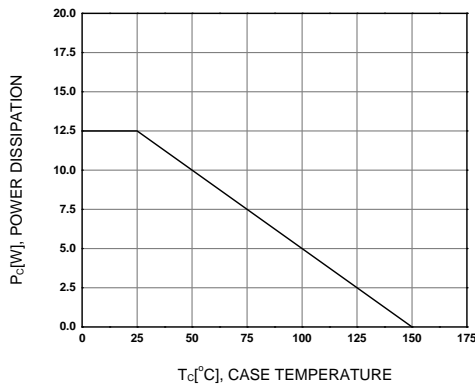
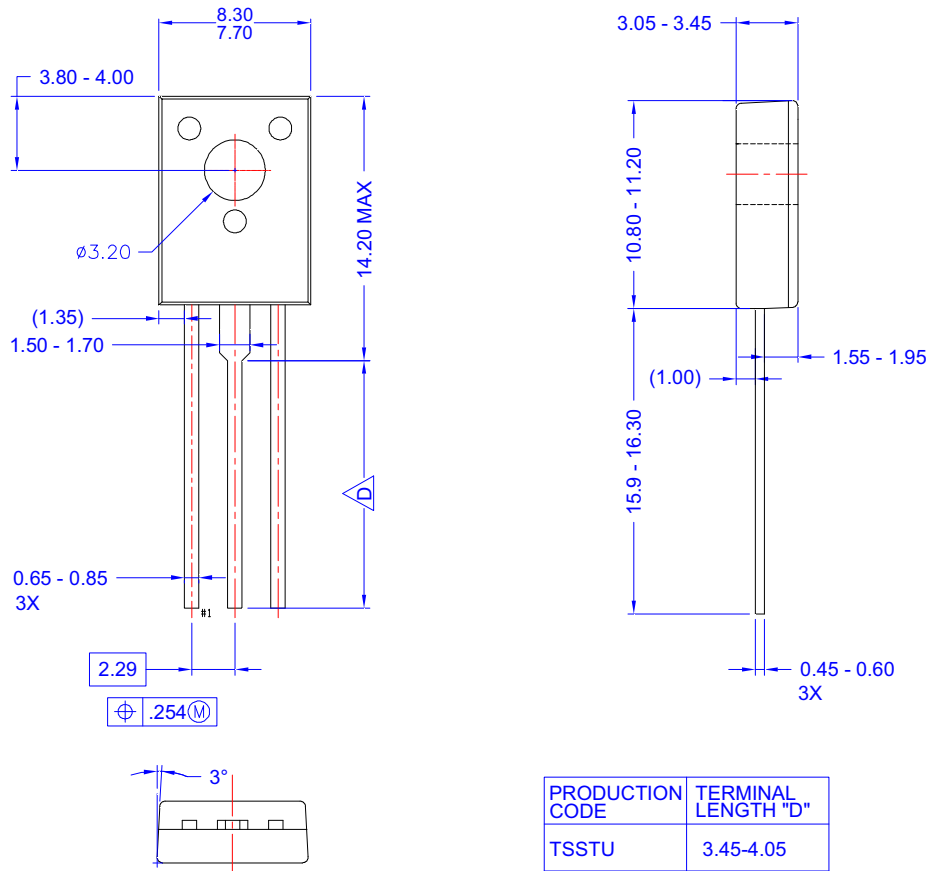


Figure 5. Power Derating

Physical Dimensions

TO-126 3L




- NOTES:
- A) THIS PACKAGE DOES NOT COMPLY TO ANY CURRENT PACKAGING STANDARD.
 - B) ALL DIMENSIONS ARE IN MILLIMETERS.
 - C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
 -  D) FOR TERMINAL LENGTH SEE TABLE
 - E) DRAWING FILE NAME AND REVISION : MKT-TO126AArev1

Figure 6. TO-126 (SOT-32) UNIFIED DRAWING (TSTU, TSSTU, STANDARD)

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